

COMPLIANT



Precision Monolithic Quad SPST CMOS Analog Switches

DESCRIPTION

The DG411 series of monolithic quad analog switches was designed to provide high speed, low error switching of precision analog signals. Combining low power (0.35 μ W) with high speed (t_{ON}: 110 ns), the DG411 family is ideally suited for portable and battery powered industrial and military applications.

To achieve high-voltage ratings and superior switching performance, the DG411 series was built on Vishay Siliconix's high voltage silicon gate process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks input voltages up to the supply levels when off.

The DG411 and DG412 respond to opposite control logic as shown in the Truth Table. The DG413 has two normally open and two normally closed switches.

FEATURES

- 44 V Supply Max Rating
- ± 15 V Analog Signal Range
- On-Resistance r_{DS(on)}: 25 Ω
- Fast Switching t_{ON}: 110 ns
- Ultra Low Power P_D: 0.35 μW
- · TTL, CMOS Compatible
- · Single Supply Capability

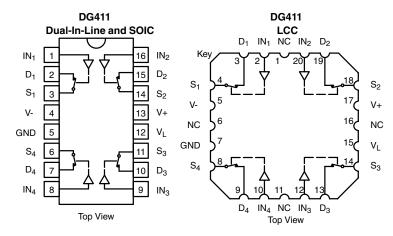
BENEFITS

- · Widest Dynamic Range
- · Low Signal Errors and Distortion
- · Break-Before-Make Switching Action
- Simple Interfacing

APPLICATIONS

- Precision Automatic Test Equipment
- Precision Data Acquisition
- · Communication Systems
- · Battery Powered Systems
- Computer Peripherals

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE					
Logic	DG411	DG412			
0	ON	OFF			
1	OFF	ON			

 $\begin{array}{l} Logic \ "0" \leq 0.8 \ V \\ Logic \ "1" \geq 2.4 \ V \end{array}$

DG413	DG413
Dual-In-Line and SOIC	LCC
	D ₁ IN ₁ NC IN ₂ D ₂
IN ₁ 1 16 IN ₂	Key 3 2 1 20 19
D ₁ 2 15 D ₂	S_1 $\searrow 4$ $\searrow 18$ $\searrow 18$ $\searrow 18$ $\searrow 18$ $\searrow 18$
S ₁ 3 9 14 S ₂	V- \sigma^5 \qquad \qquad \qquad \qquad \qquad \qquad \qquad \qquad \qqqqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq \qqq \qqqq
V- 4 13 V+	$_{\rm NC}$ $\left\{ 6 \right\}_{\rm NC}$
GND 5 12 V _L	$_{\text{GND}}$ \int_{7}^{7} $_{15}$ $_{\text{V}_{\text{L}}}$
S ₄ 6 11 S ₃	S_4 S_4 S_5 S_4 S_5
D_4 7 10 D_3	
IN ₄ 8 9 IN ₃	9 10 11 12 13
Top View	D_4 IN_4 NC IN_3 D_3 Top $View$

TRUTH TABLE					
Logic	SW ₁ , SW ₄	SW ₂ , SW ₃			
0	OFF	ON			
1	ON	OFF			

 $\begin{array}{l} \text{Logic "0"} \leq 0.8 \text{ V} \\ \text{Logic "1"} \geq 2.4 \text{ V} \end{array}$

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^{*} Pb containing terminations are not RoHS compliant, exemptions may apply



ORDERING INFORMATION					
Temp Range	Package	Part Number			
DG411/DG412					
- 40 to 85 °C	16-Pin Plastic DIP	DG411DJ DG411DJ-E3			
	וס-רווו רומטונל טור	DG412DJ DG412DJ-E3			
- 40 to 85 °C	16-Pin Narrow SOIC	DG411DY DG411DY-E3 DG411DY-T1 DG411DY-T1-E3			
	16-Pin Narrow SOIC	DG412DY DG412DY-E3 DG412DY-T1 DG412DY-T1-E3			
DG413					
- 40 to 85 °C	16-Pin Plastic DIP	DG413DJ DG413DJ-E3			
	16-Pin Narrow SOIC	DG413DY DG413DY-E3 DG413DY-T1 DG413DY-T1-E3			

ABSOLUTE MAXIMUM	I RATINGS			
Parameter		Limit	Unit	
V+ to V-		44		
GND to V-		25		
V_{L}		(GND - 0.3) to (V+) + 0.3	V	
Digital Inputs ^a , V _S , V _D		(V-) -2 to (V+) + 2 or 30 mA, whichever occurs first		
Continuous Current (Any Terminal)		30	mA	
Peak Current, S or D (Pulsed at 1 ms, 10 % duty cycle)		100	IIIA	
Storage Temperature	(AK, AZ Suffix)	- 65 to 150	°C	
Storage Temperature	(DJ, DY Suffix)	- 65 to 125	l	
	16-Pin Plastic DIP ^c	470		
Power Dissipation (Package) ^b	16-Pin Narrow SOIC ^d	600	mW	
	16-Pin CerDIP ^e	900	11100	
	LCC-20 ^e	900		

Notes:

- $a. \ Signals \ on \ S_X, \ D_X, \ or \ IN_X \ exceeding \ V+ \ or \ V- \ will \ be \ clamped \ by \ internal \ diodes. \ Limit \ forward \ diode \ current \ to \ maximum \ current \ ratings.$
- b. All leads welded or soldered to PC Board.
- c. Derate 6 mW/°C above 25 °C.
- d. Derate 7.6 mW/°C above 75 °C.
- e. Derate 12 mW/°C above 75 °C.



SPECIFICATIONS ^a									
		Test Conditions Unless Specified V+ = 15 V, V- = - 15 V			A Suffix - 55 to 125 °C		D Suffix - 40 to 85 °C		
Parameter	Symbol	$V_L = 5 \text{ V}, V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^f$	Tempb	Typ ^c	Min ^d	Max ^d	Min ^d	Max ^d	Unit
Analog Switch	- 1				1	l	I	I	I
Analog Signal Range ^e	V _{ANALOG}		Full		- 15	15	- 15	15	V
Drain-Source On-Resistance	r _{DS(on)}	V+ = 13.5 V, V- = -13.5 V $I_S = -10 \text{ mA}, V_D = \pm 8.5 \text{ V}$	Room Full	25		35 45		35 45	Ω
Switch Off Leakage Current	I _{S(off)}	V+ = 16.5, V- = - 16.5 V	Room Full	± 0.1	- 0.25 - 20	0.25 20	- 0.25 - 5	0.25 5	
ownon on Loundge outlone	I _{D(off)}	$V_D = \pm 15.5 \text{ V}, V_S = \pm 15.5 \text{ V}$	Room Full	± 0.1	- 0.25 - 20	0.25 20	- 0.25 - 5	0.25 5	nA
Channel On Leakage Current	I _{D(on)}	V+ = 16.5 V, V- = -16.5 V $V_S = V_D = \pm 15.5 V$	Room Full	± 0.1	- 0.4 - 40	0.4 40	- 0.4 - 10	0.4 10	
Digital Control									
Input Current, V _{IN} Low	I _{IL}	V _{IN} under test = 0.8 V	Full	0.005	- 0.5	0.5	- 0.5	0.5	μA
Input Current, V _{IN} High	I _{IH}	V _{IN} under test = 2.4 V	Full	0.005	- 0.5	0.5	- 0.5	0.5	μΛ
Dynamic Characteristics									
Turn-On Time	t _{ON}	$R_L = 300 \Omega, C_L = 35 pF$	Room Full	110		175 240		175 220	
Turn-Off Time	t _{OFF}	$V_S = \pm 10 \text{ V}$, See Figure 2	Room Full	100		145 160		145 160	ns
Break-Before-Make Time Delay	t _D	DG413 Only, $V_S = 10 \text{ V}$ $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$	Room	25					
Charge Injection	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega$ $C_L = 10 \text{ nF}$	Room	5					рС
Off Isolation ^e	OIRR	$R_L = 50 \Omega, C_L = 5 pF,$	Room	68					
Channel-to-Channel Crosstalk ^e	X _{TALK}	f = 1 MHz	Room	85					dB
Source Off Capacitance ^e	C _{S(off)}		Room	9					
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	Room	9					pF
Channel On Capacitance ^e	C _{D(on)}		Room	35					
Power Supplies			•						
Positive Supply Current	l+		Room Full	0.0001		1 5		1 5	
Negative Supply Current	l-	V+ = 16.5 V, V- = - 16.5 V	Room Full	- 0.0001	- 1 - 5		- 1 - 5		μA
Logic Supply Current	ΙL	$V_{IN} = 0 \text{ or } 5 \text{ V}$	Room Full	0.0001		1 5		1 5	μΛ
Ground Current	I _{GND}		Room Full	- 0.0001	- 1 - 5		- 1 - 5		



SPECIFICATIONS F	OR UNIP	OLAR SUPPLIES ^a							
		Test Conditions Unless Specified			A Suffix - 55 to 125 °C		D Suffix - 40 to 85 °C		
Parameter	Symbol	V+ = 12 V, V- = 0 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^f$	Temp ^b	Typ ^c	Min ^d	Max ^d	Min ^d	Max ^d	Unit
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full			12		12	V
Drain-Source On-Resistance	r _{DS(on)}	V+ = 10.8 V, $I_S = -10 \text{ mA}, V_D = 3 \text{ V}, 8 \text{ V}$	Room Full	40		80 100		80 100	Ω
Dynamic Characteristics	1			I.	•		•	•	
Turn-On Time	t _{ON}	$R_L = 300 \Omega$, $C_L = 35 pF$	Room Hot	175		250 400		250 315	
Turn-Off Time	t _{OFF}	$V_S = 8 V$, See Figure 2	Room Hot	95		125 140		125 140	ns
Break-Before-Make Time Delay	t _D	DG413 Only, $V_S = 8 \text{ V}$ $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$	Room	25					
Charge Injection	Q	$V_g = 6 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	25					рС
Power Supplies	1			I.	•		•	•	
Positive Supply Current	I+		Room Hot	0.0001		1 5		1 5	
Negative Supply Current	I-	V. 125 V.V. 0 or 5 V	Room Hot	- 0.0001	- 1 - 5		- 1 - 5		
Logic Supply Current	IL	$V+ = 13.5 \text{ V}, V_{1N} = 0 \text{ or } 5 \text{ V}$	Room Hot	0.0001		1 5		1 5	μA
Ground Current	I _{GND}		Room Hot	- 0.0001	- 1 - 5		- 5		

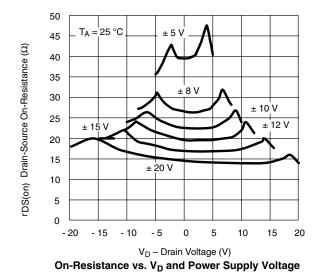
Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b.Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e.Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

300

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

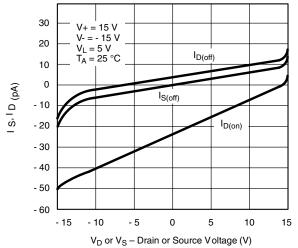


 $V_L = 5 V$ 250 V + = 3 V $V_L = 3 V$ 200 $V_{DS(on)}(\Omega)$ 150 V+ = 5 V 100 8 V 50 15 V 20 V 0 4 8 10 12 14 16 V_D – Drain Voltage (V)

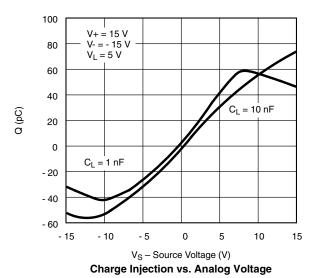
On-Resistance vs. V_D and Unipolar Supply Voltage

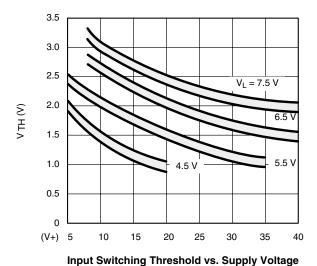


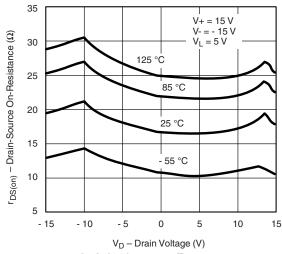
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



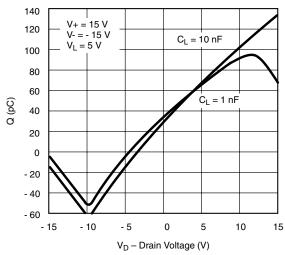
Leakage Current vs. Analog Voltage



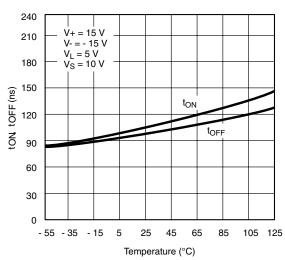




I_D, I_S Leakages vs. Temperature



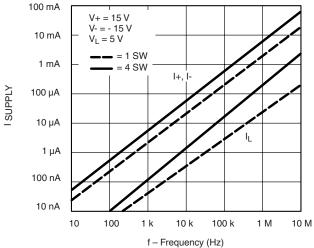
Charge Injection vs. Analog Voltage



Switching Time vs. Temperature

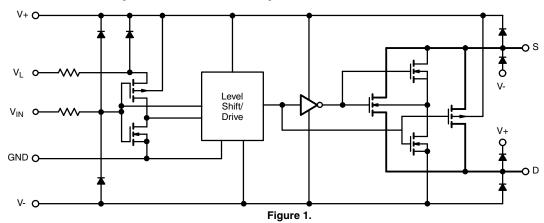
VISHAY.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Supply Current vs. Input Switching Frequency

SCHEMATIC DIAGRAM (TYPICAL CHANNEL)



TEST CIRCUITS

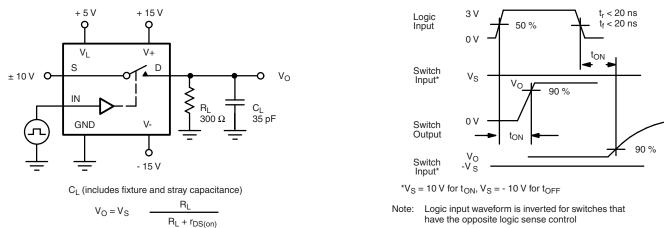
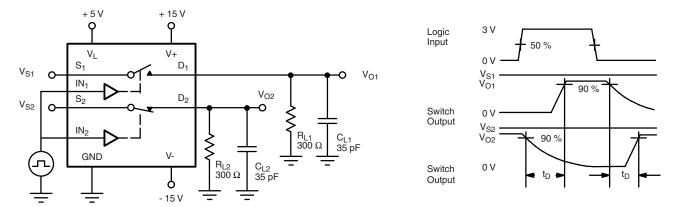


Figure 2. Switching Time



TEST CIRCUITS



C_L (includes fixture and stray capacitance)

Figure 3. Break-Before-Make (DG413)

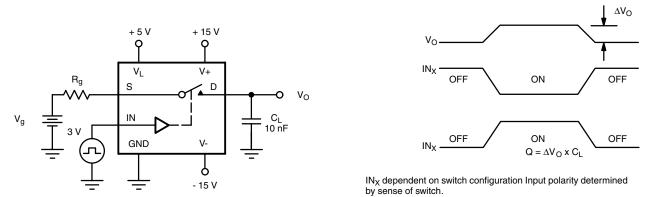


Figure 4. Charge Injection

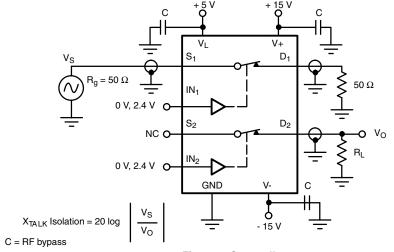


Figure 5. Crosstalk



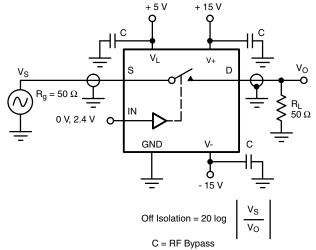


Figure 6. Off Isolation

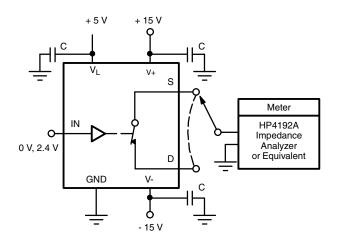


Figure 7. Source/Drain Capacitances

APPLICATIONS

Single Supply Operation:

The DG411/412/413 can be operated with unipolar supplies from 5 V to 44 V. These devices are characterized and tested for unipolar supply operation at 12 V to facilitate the majority of applications. In single supply operation, V+ is tied to V_L and V- is tied to 0 V. See Input Switching Threshold vs. Supply Voltage curve for V_L versus input threshold requirments.

Summing Amplifier

When driving a high impedance, high capacitance load such as shown in Figure 8, where the inputs to the summing amplifier have some noise filtering, it is necessary to have shunt switches for rapid discharge of the filter capacitor, thus preventing offsets from occurring at the output.

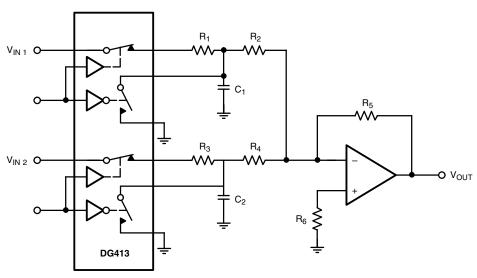


Figure 8. Summing Amplifier

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